

PSD11 The 11th International Conference on Position Sensitive Detectors

Silicon Detectors for Beam Characterization Move IT

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Introduction

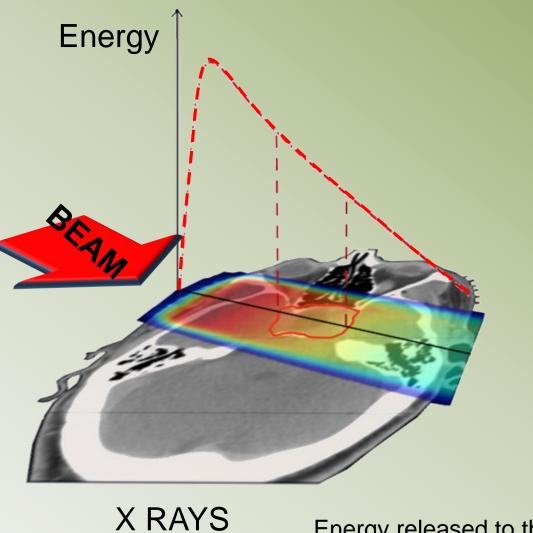


Modeling and Verification for IonOVe ITbeam Treatment planning

Interdisciplinary project involving the collaboration of various INFN groups and the three Italian hadron therapy facilities (CNAO, LNS, TIFPA).



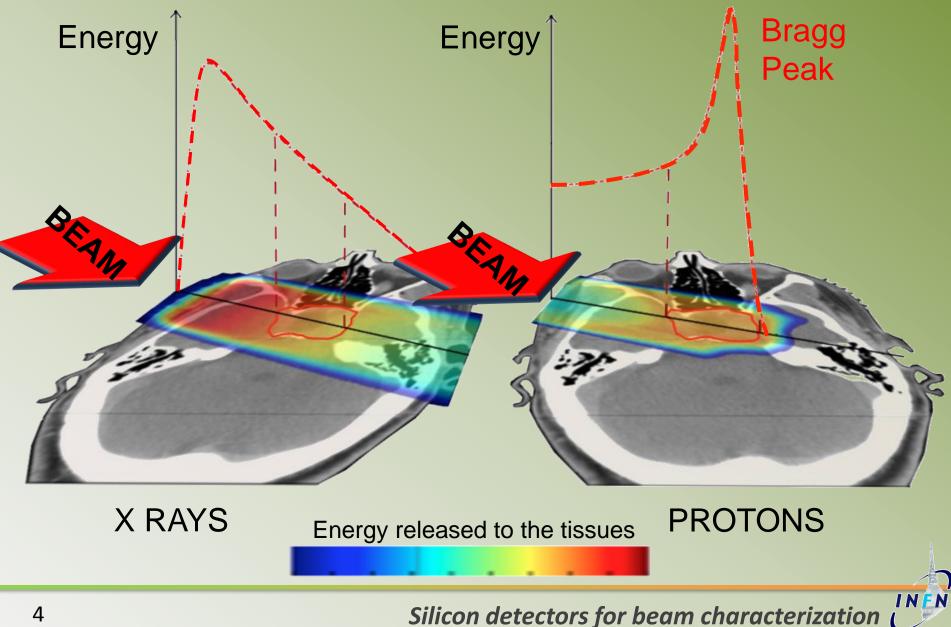
Developing innovative silicon detectors optimized for excellent time resolutions (Ultra Fast Silicon Detectors, UFSDs) to characterize and monitor therapeutic ion beams, overcoming the limits of ionization chambers.

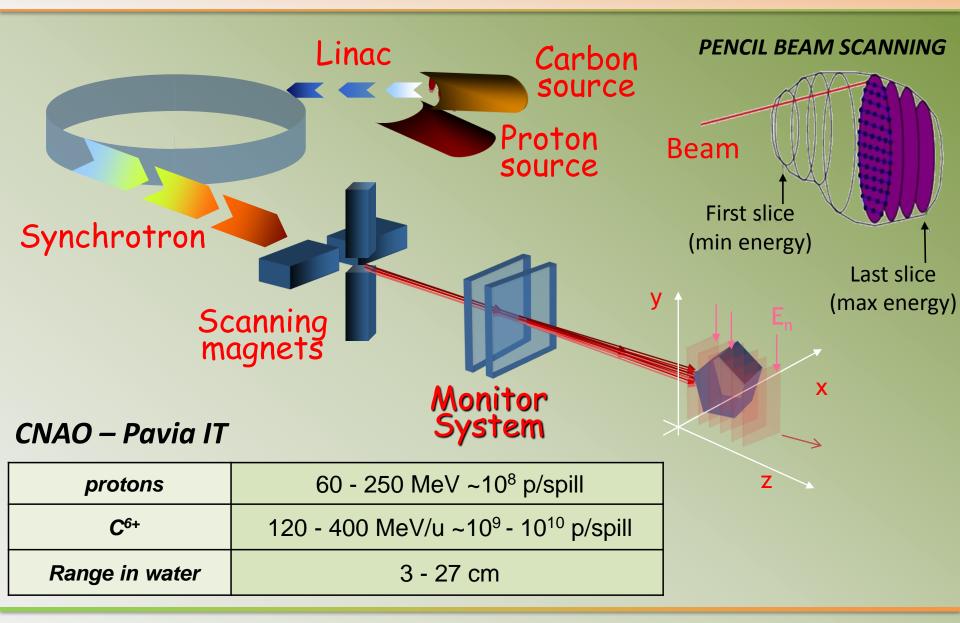


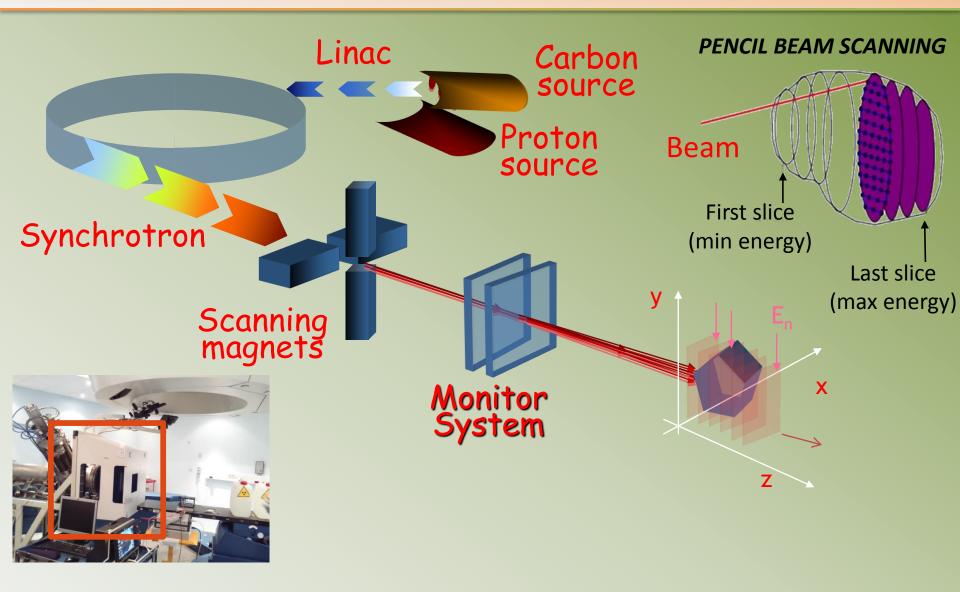
Energy released to the tissues

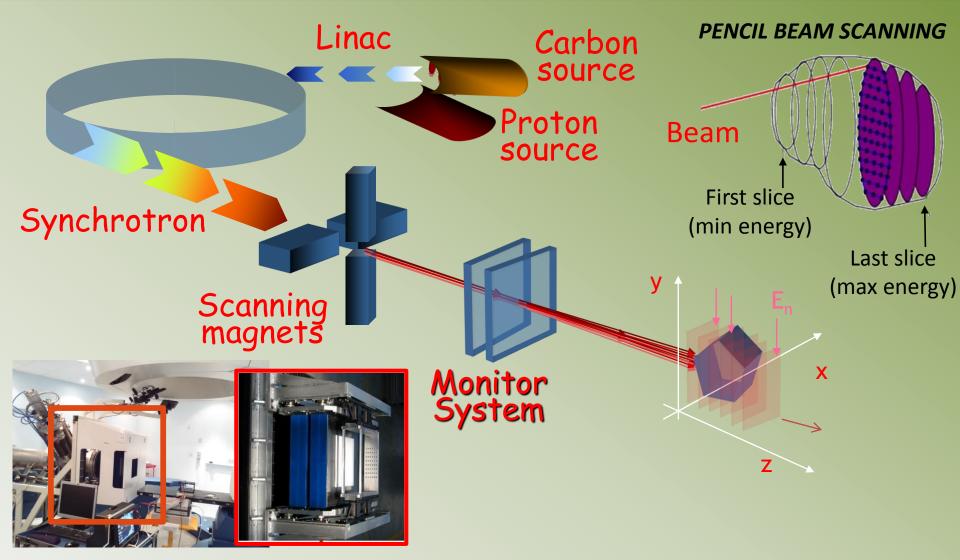
Silicon detectors for beam characterization

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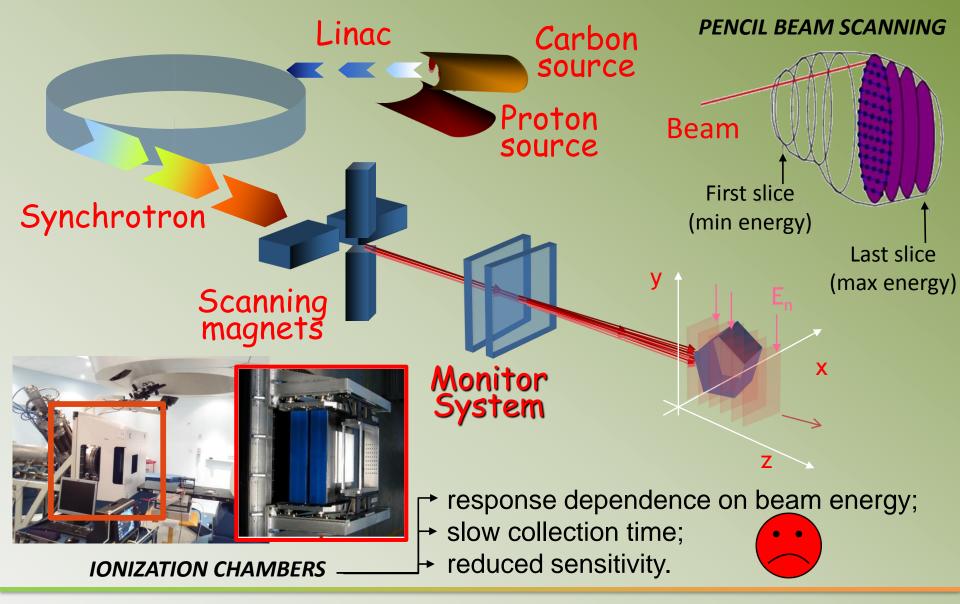




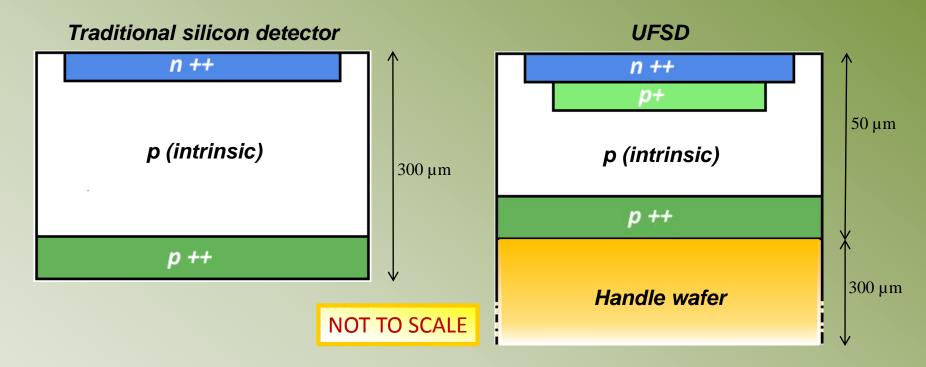




IONIZATION CHAMBERS



Introduction: Ultra Fast Silicon Detector (UFSD)



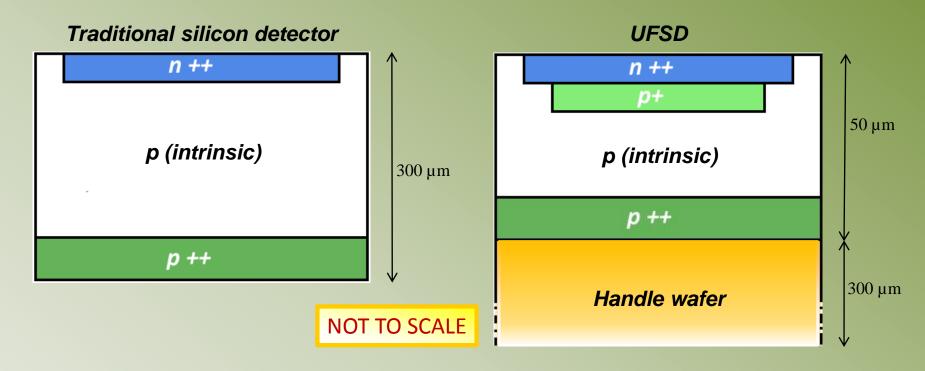
 ✓ controlled low gain (based on LGAD, Low-Gain Avalanche Detectors);

✓ excellent time resolutions.

H.F.-W. Sadrozinski et al. Ultra-fast silicon detectors (UFSD) Nucl. Instrum. Meth. A831 (2016) 18-23.

V. Sola et al. Ultra-Fast Silicon Detectors for 4D tracking. Journal of Instrumentation (2017), Volume 12.

Introduction: Ultra Fast Silicon Detector (UFSD)



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Thickness of ~50 micron and gain of ~20 result in optimum performance.

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Two UFSD devices are being developed:

- to directly count individual protons at high rates and (thanks to the segmentation in strips) to measure the beam profiles in two orthogonal directions;
- to measure the beam energy with time-of-flight techniques, using a telescope of two UFSD sensors segmented in a minimum number of pads.

Aim – Near future

...clinical application is very far...

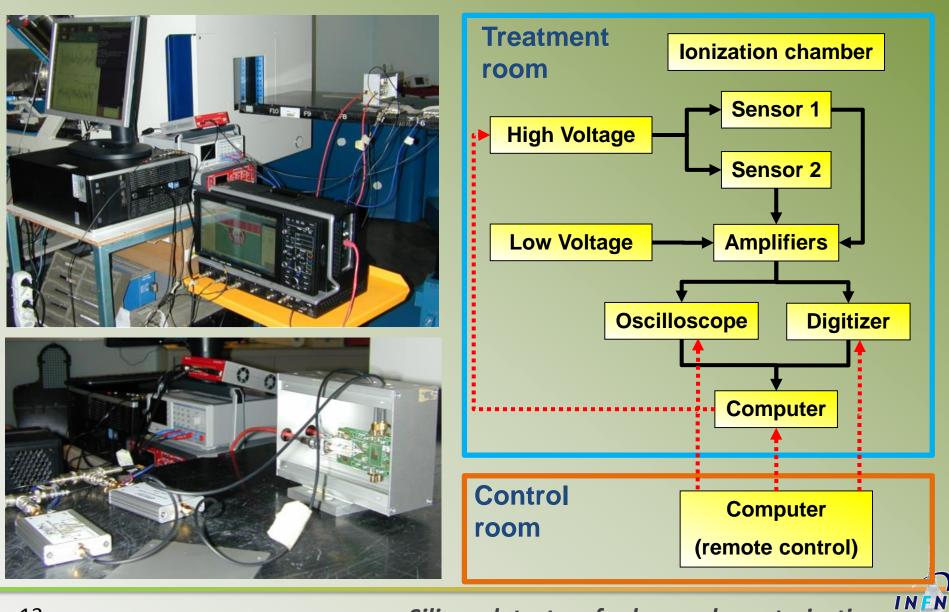




Passive scattering technique \rightarrow FOV 3x3 cm²;

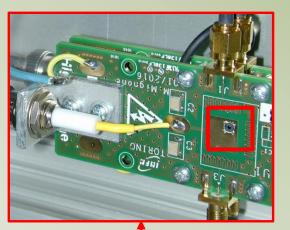
 $Flux = 10^8 p/s cm^2$

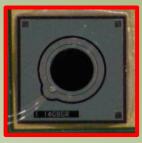
Beam tests



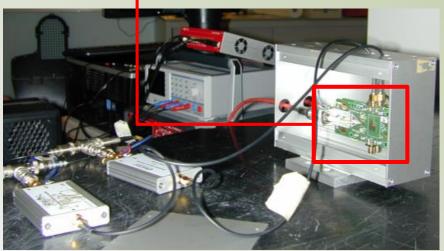
Beam tests

2 detectors of 50 μm:
1. CNM 1,2 x 1,2 mm²;
2. Hamamatsu Ø1 mm.





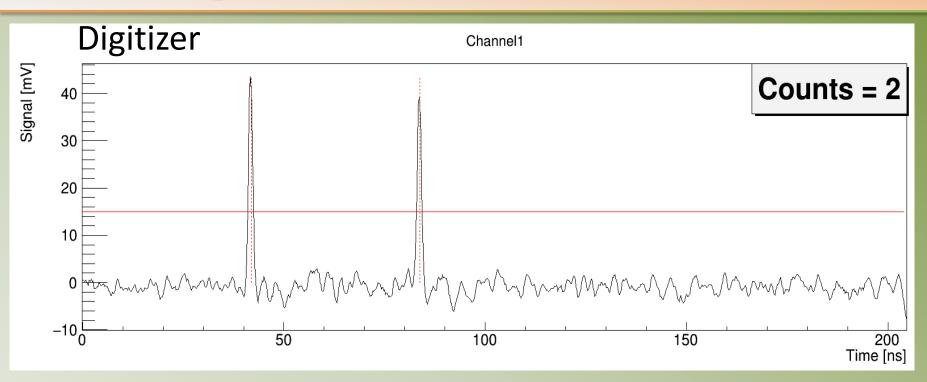




- ✓ CNAO (Pavia);
- ✓ 32 runs;
- ✓ ~ 2*10¹⁰ p each run (FWHM 1 cm);
- ✓ protons (62-227 MeV);
- ✓ Different fluxes

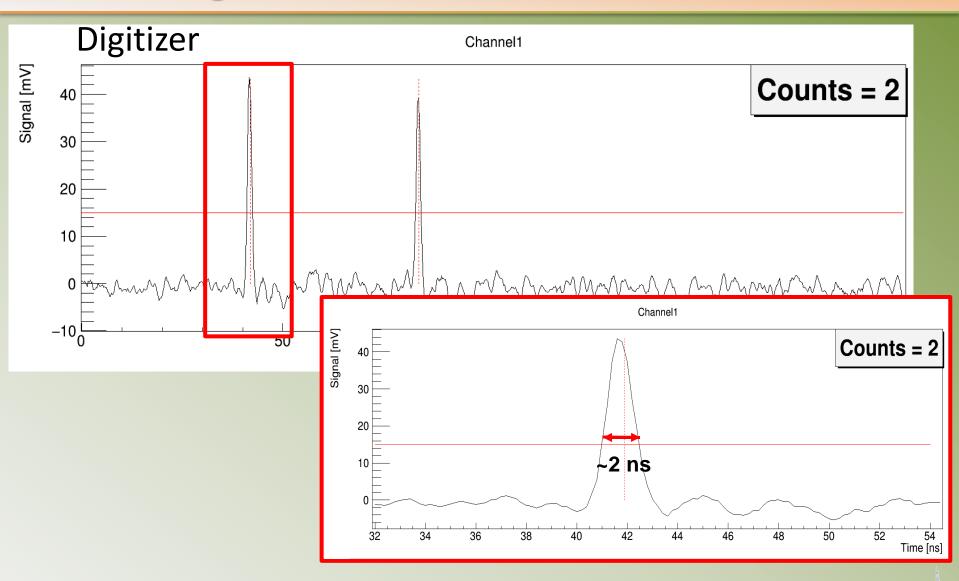
(Degrader 20-100).

Results – Signal Duration



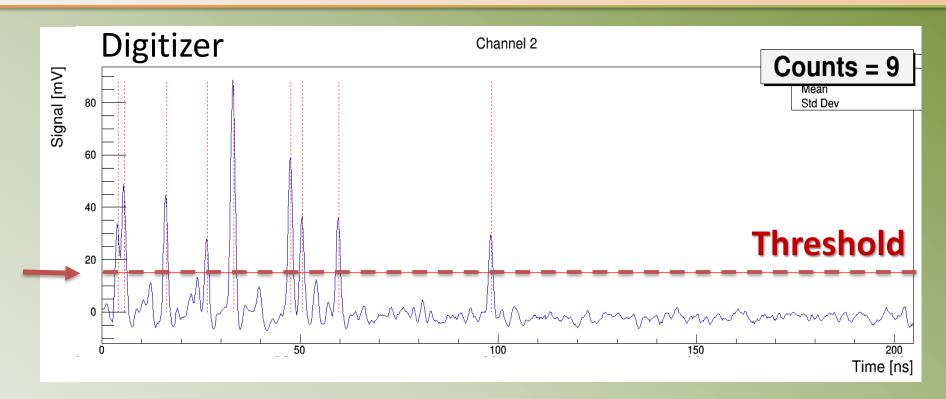
Silicon detectors for beam characterization

Results – Signal Duration



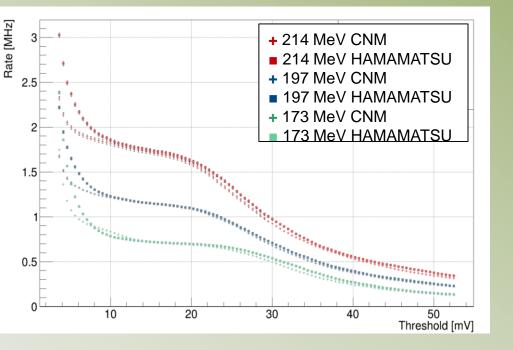
Silicon detectors for beam characterization

Results – Threshold and Pile up



Silicon detectors for beam characterization

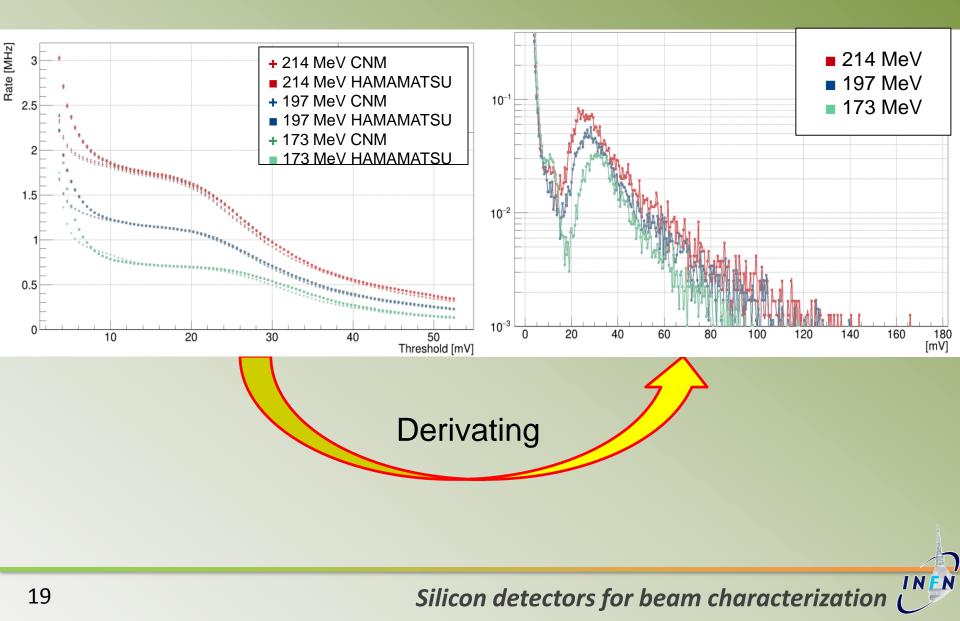
Results – Threshold



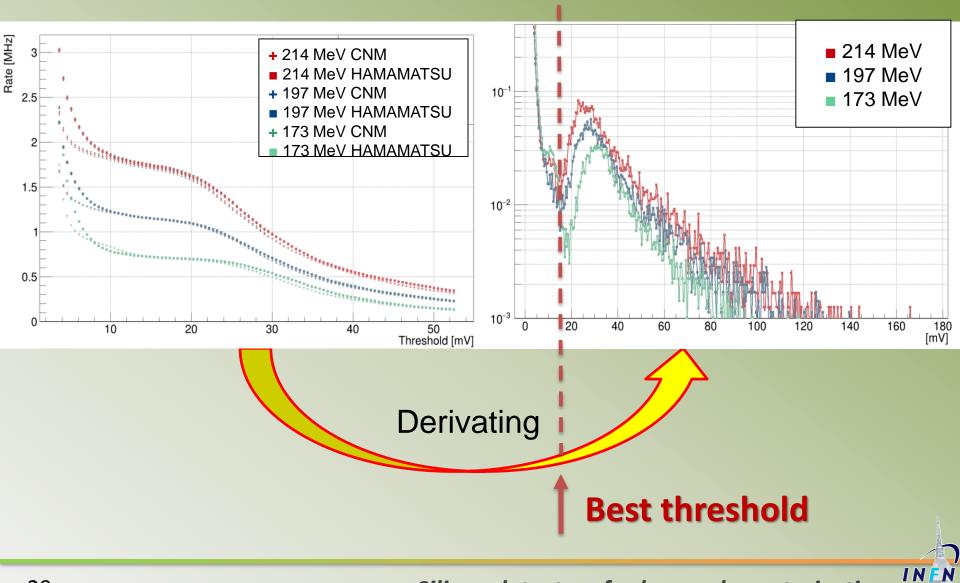
Silicon detectors for beam characterization

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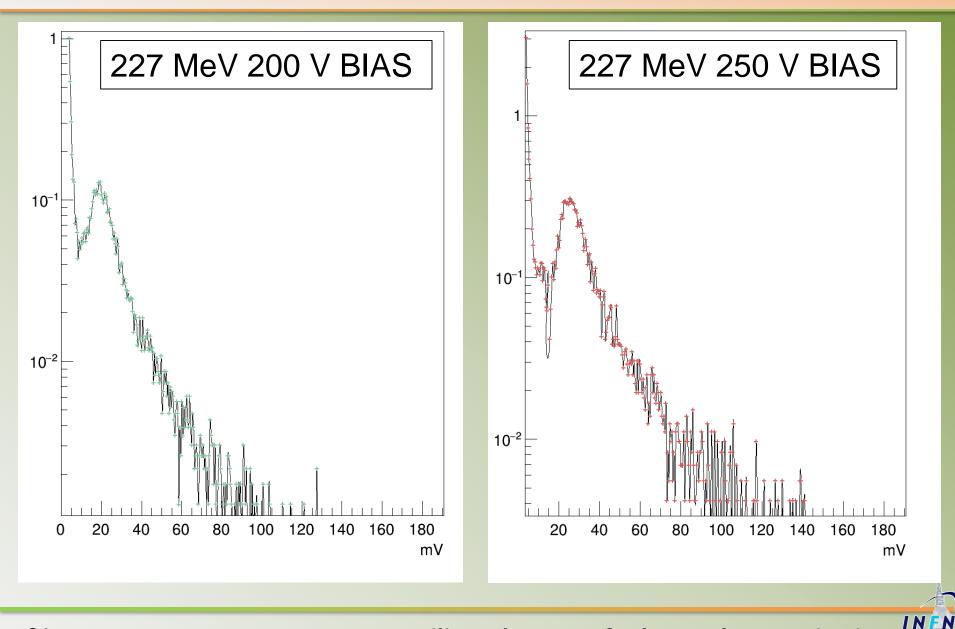
Results – Threshold



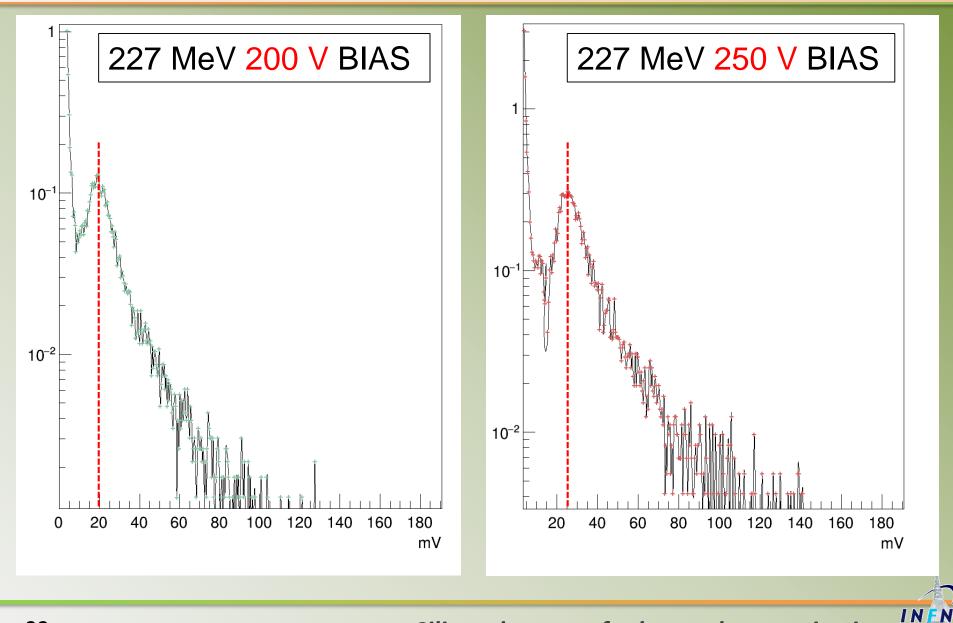
Results – Threshold



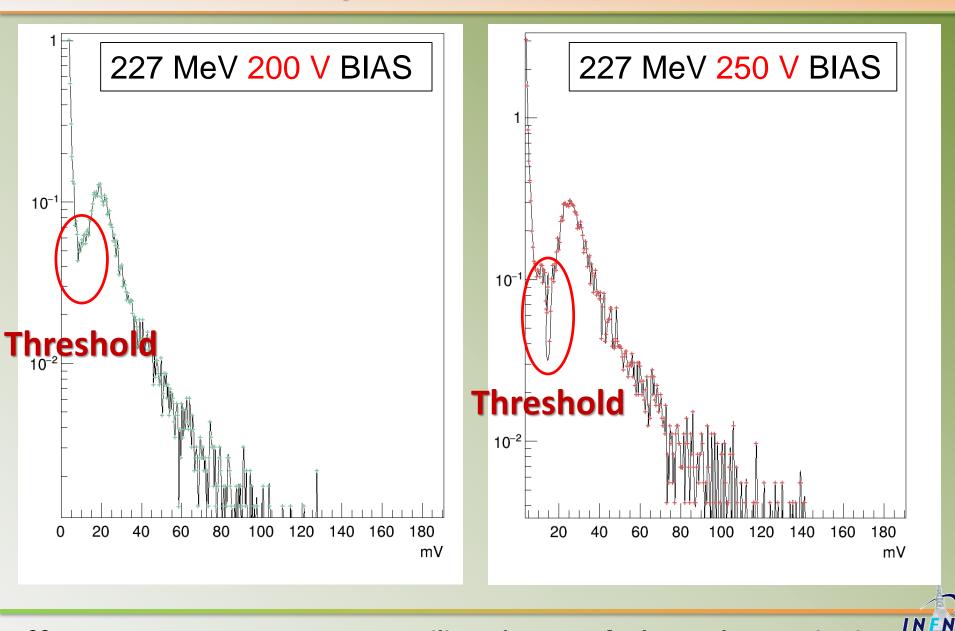
Results – Possibility to enhance S/N ratio



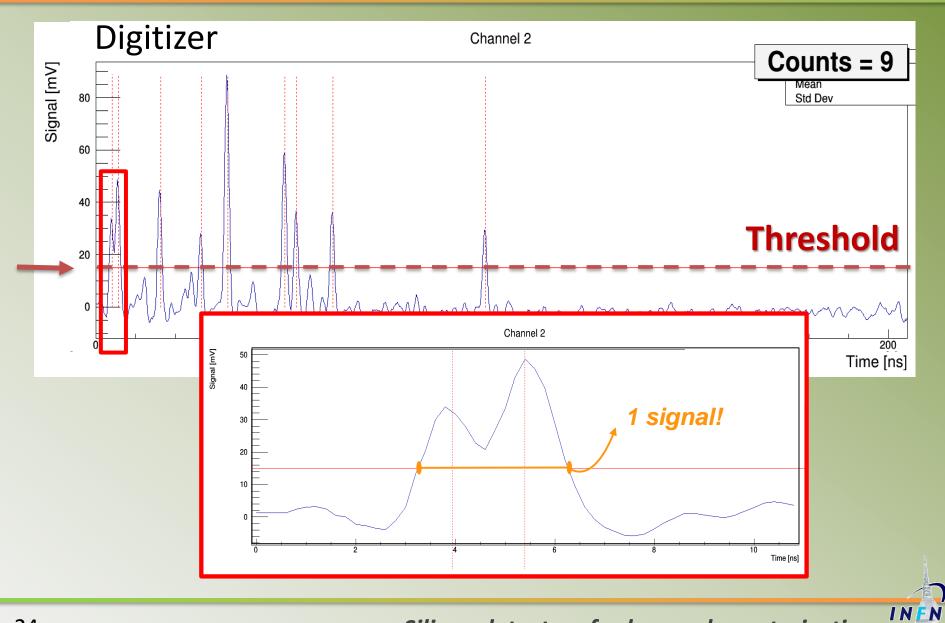
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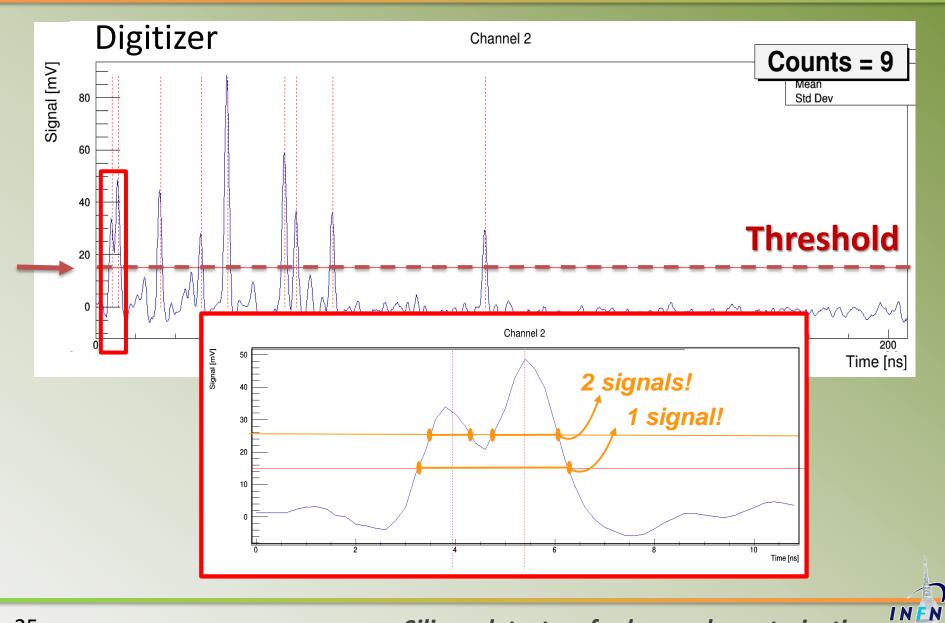
Results – Possibility to enhance S/N ratio

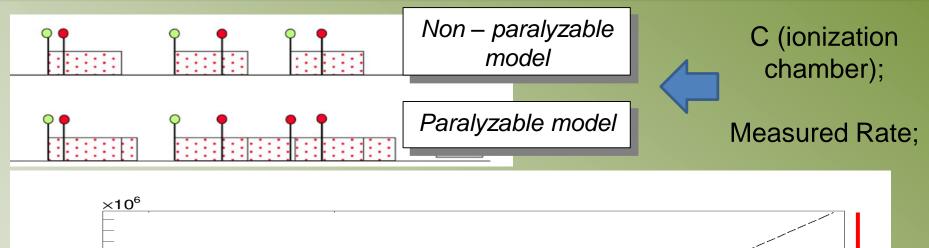


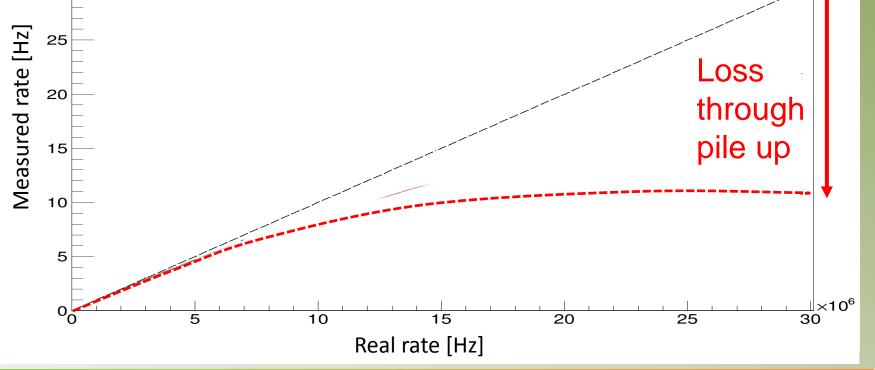
Results – Pile up



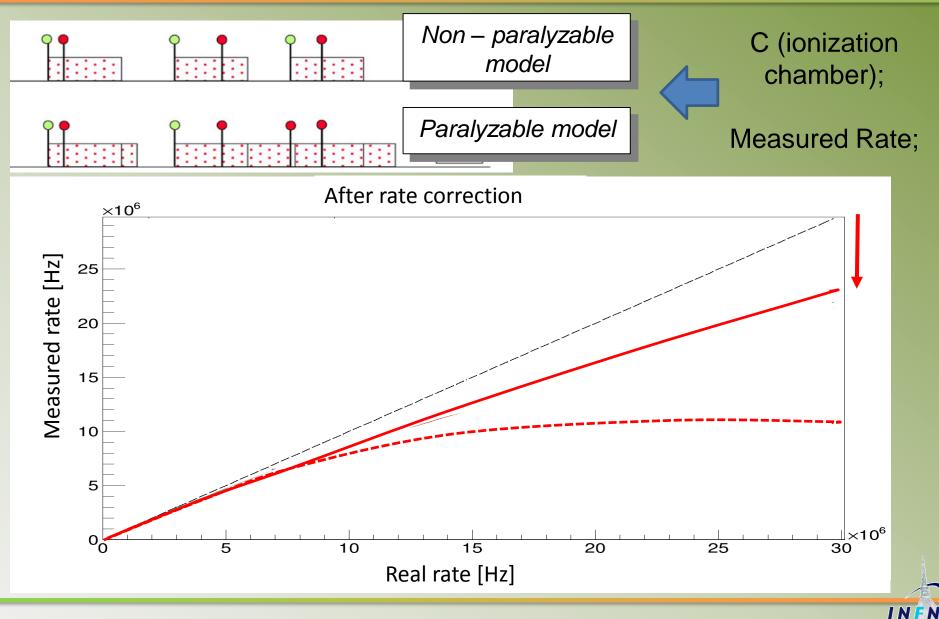
Results – Pile up

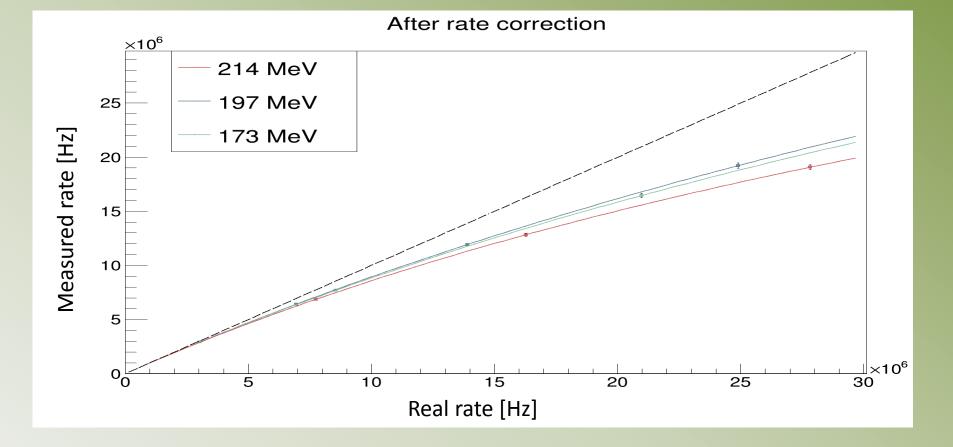


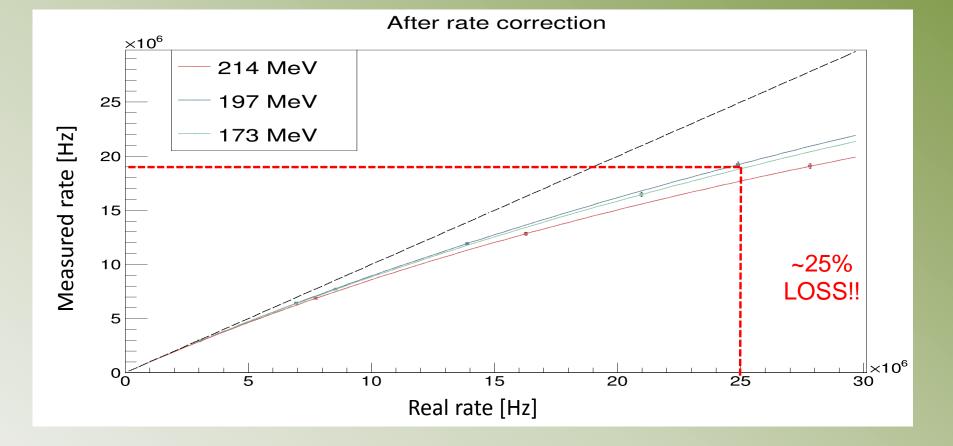




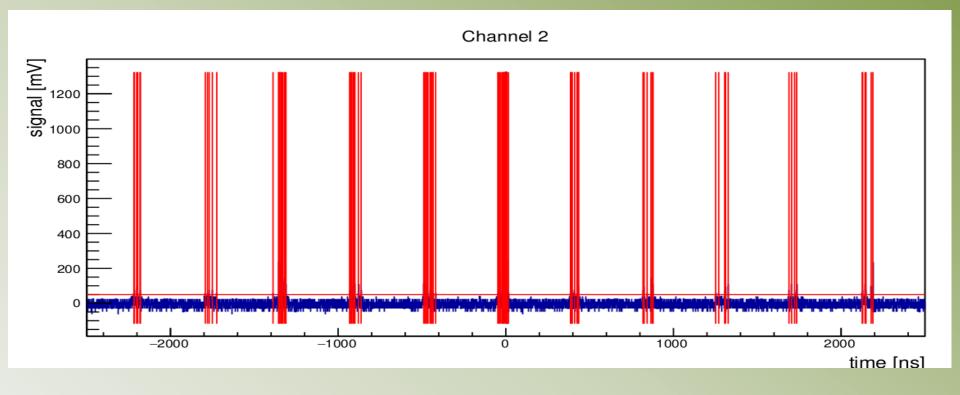
Silicon detectors for beam characterization







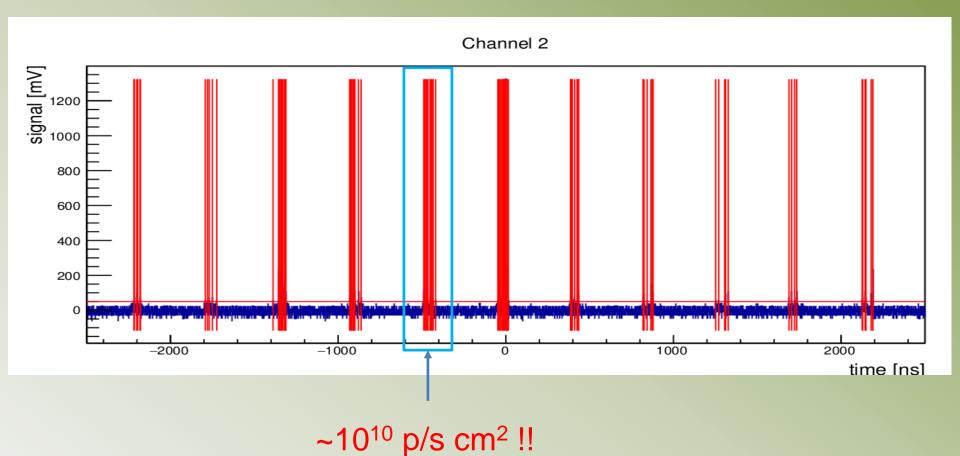
Results – Bunched structure of the beam



Silicon detectors for beam characterization

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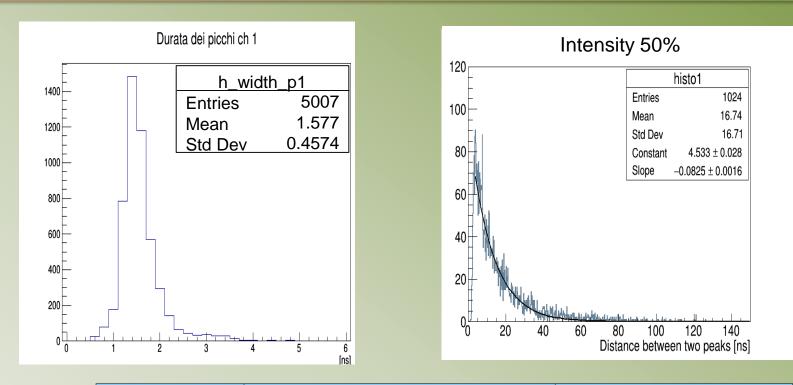
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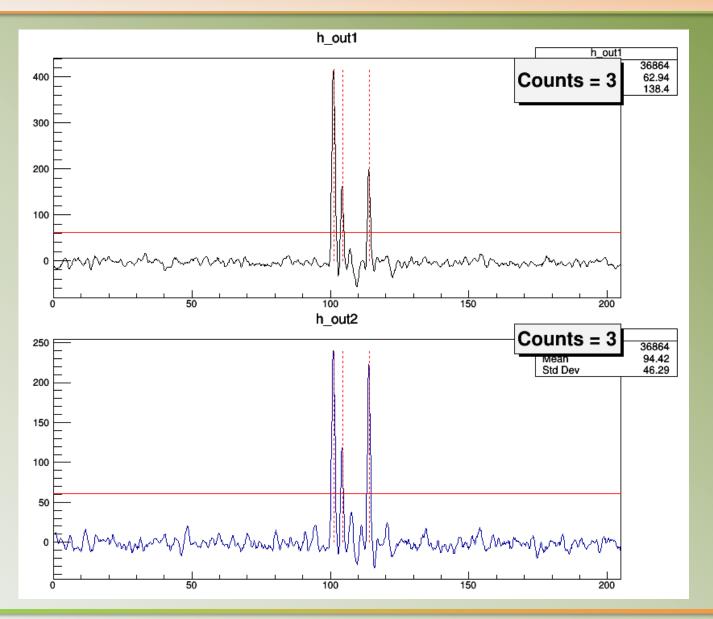
Results – Bunched structure of the beam



Intensity	Rate (counts) [MHz]	Rate (fit) [MHz]
20%	2.92 ± 0.03	50.7 ± 1.1
50%	7.70 ± 0.09	82.5 ± 1.6
100%	13.57 ± 0.21	127.3 ± 2.6

Silicon detectors for beam characterization

Results – Sensors correlation

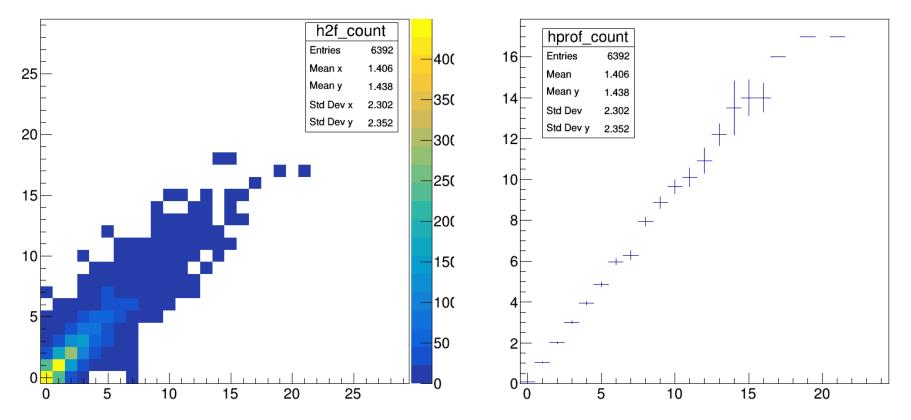


Silicon detectors for beam characterization

Results – Sensors correlation

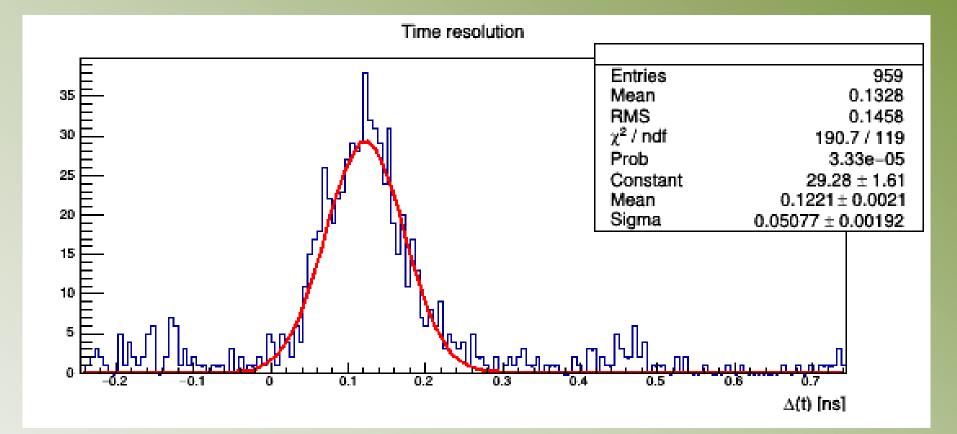
Count on Ch 1 and Ch 2

Profile of Ch2 versus Ch1



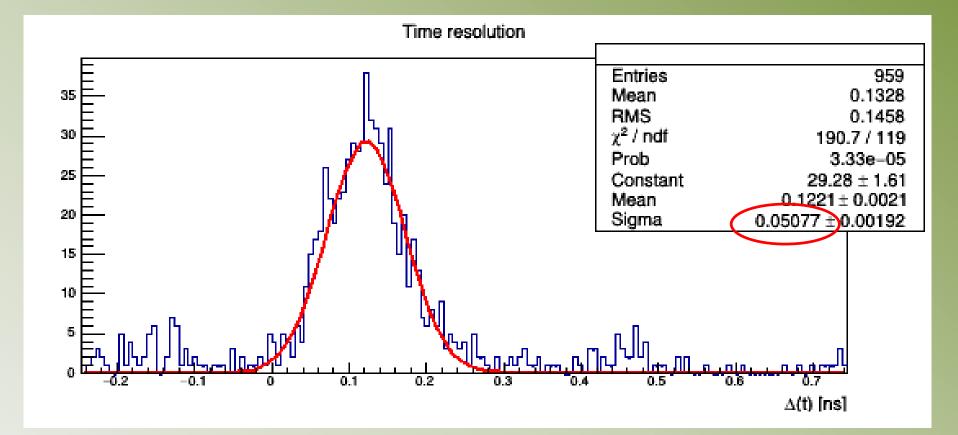
Silicon detectors for beam characterization

Results – Time resolution



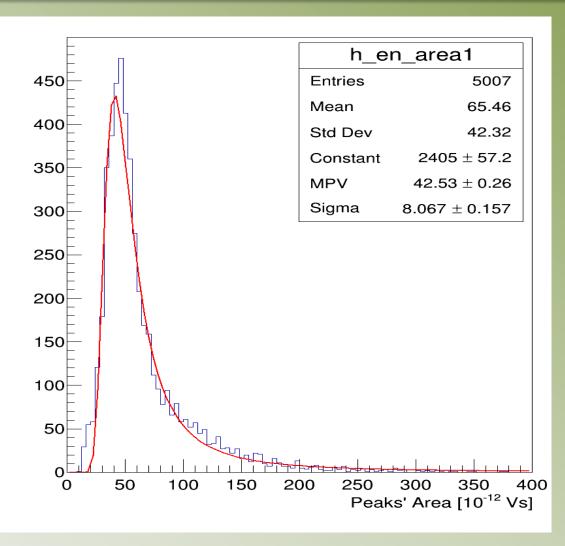
Silicon detectors for beam characterization

Results – Time resolution



Silicon detectors for beam characterization

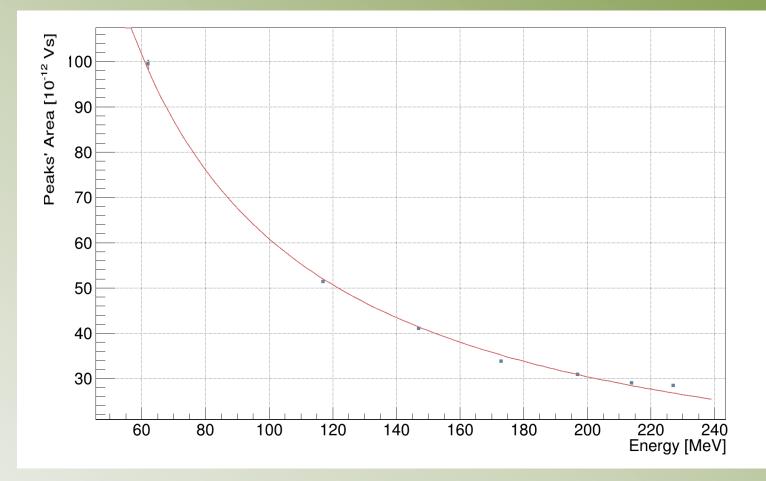
Results – Landau



Silicon detectors for beam characterization

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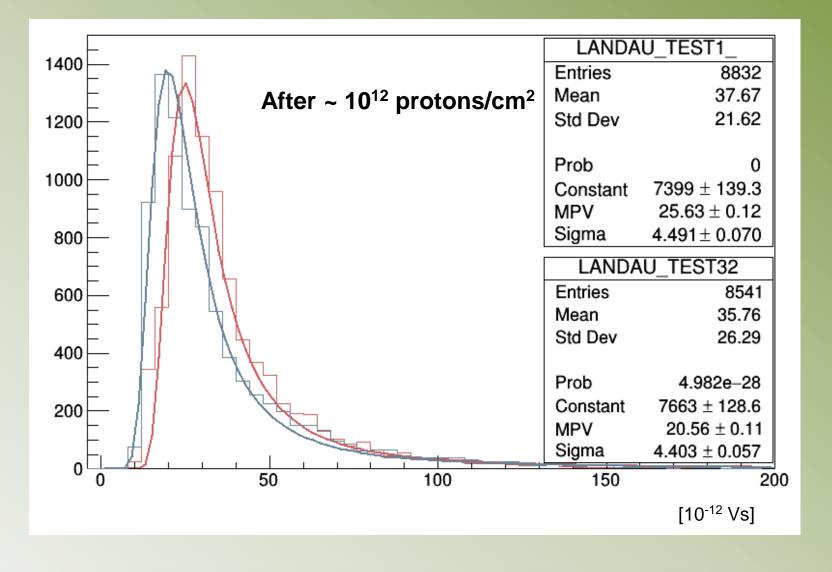
Results – MPV distribution



Bethe-Bloch curve's trend

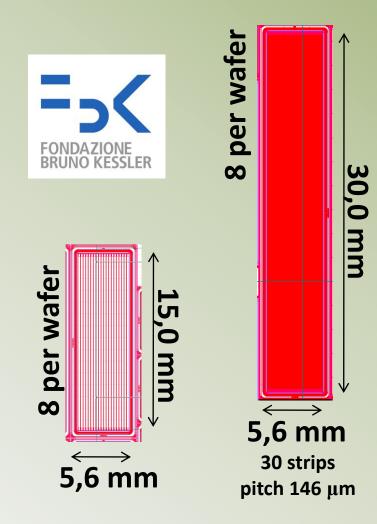
Silicon detectors for beam characterization

Results – Radiation damage



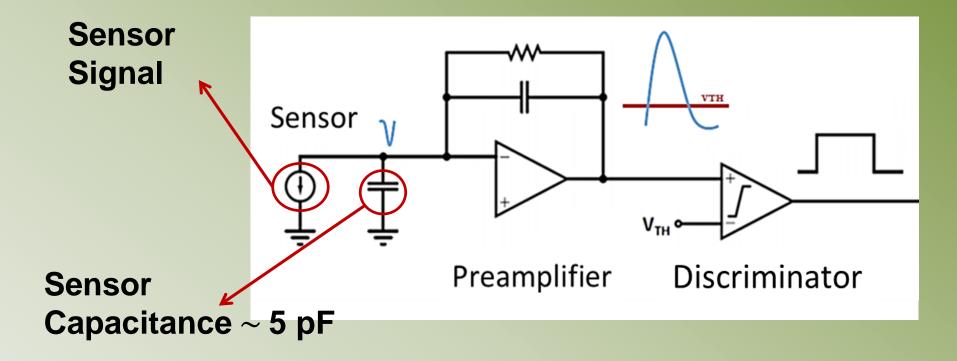
Silicon detectors for beam characterization

Ongoing – Strips sensors and doping possibilities



- ✓ Different doping doses;
- Doping with gallium instead of boron;
- Treatment with a carbon spray;
- Varying the thermal cycle for activation.

Ongoing – Fast front-end electronics



Proton beam energy range: $60\div250 \text{ MeV} (6-2 \text{ MIPs})$ Front-End Input charge range: 3 fC ÷ 130 fC Fluxes measurements: up to $10^8 \text{ p cm}^{-2} \text{ s}^{-1}$ Pile-up probability kept < 1 %.

UFSD in charge particle therapy could open new perspectives:

Directly count the number of particles \rightarrow exploiting the large UFSD S/N ratio and fast collection time in small thicknesses;

Measure the energy of the beam \rightarrow exploiting the outstanding time resolution.



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OVe IT

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Thank you

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